MOOV

Item settings	Standard/Optional Parameters
Laser light source (Exposure Source)	• **375 nm** semi-guided laser (optional/dual light source)
Patterned solutions	• Minimum feature size (CD): 0.45 ÿm • Writing grid size: 10nm
Alignment System (Alignment System)	• 3 Camera Systems (Overview, Macro, Micro) • Forward-facing (TSA) accuracy: ÿ **250 nm** • Back alignment (BSA) accuracy: ÿ **500 nm**
Focal length control Ru (Focus System)	• Pressure-based real-time dynamic autofocus Pneumatic Focus • Optical Focus
Carriers and Automakers Chon (Substrate Handling)	• Wafer size: 2 x 2 mm fragments, maximum **6 inches (150 mm)** • Thickness range: 100 ÿm to 6 mm • Option: Autoloader
Write speed (Throughput)	• 100 x 100 mm area: < 10 min • 150 mm complete wafer: < **16** point